Elektronische Bauelemente

MMBTA94

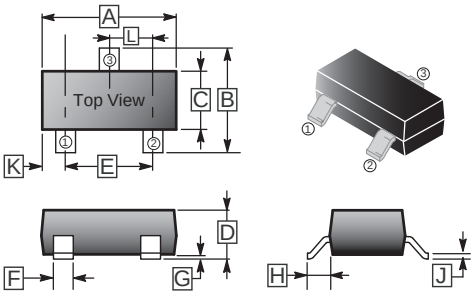
PNP Silicon
-400V, -0.1A, 350mW
Epitaxial Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

SOT-23

FEATURES

- High Voltage Transistor

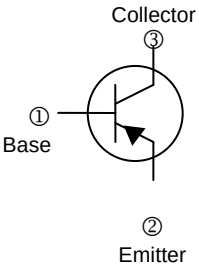


MARKING

4D

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-23	3K	7 inch



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.04	G	-	0.18
B	2.10	2.80	H	0.40	0.60
C	1.20	1.60	J	0.08	0.20
D	0.89	1.40	K	0.6 REF.	
E	1.78	2.04	L	0.85	1.15
F	0.30	0.50			

MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

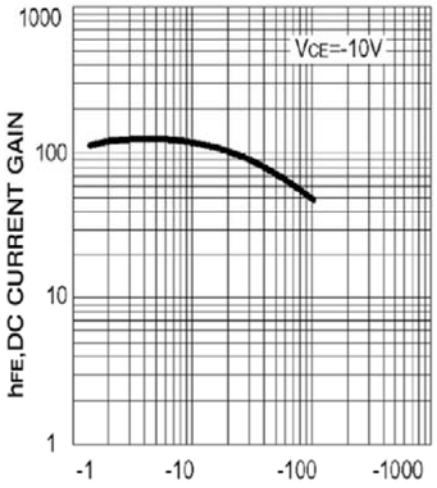
PARAMETER	SYMBOL	RATINGS	UNIT
Collector - Base Voltage	V_{CBO}	-400	V
Collector - Emitter Voltage	V_{CEO}	-400	V
Emitter - Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-0.1	A
Collector Power Dissipation	P_C	350	mW
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	℃

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

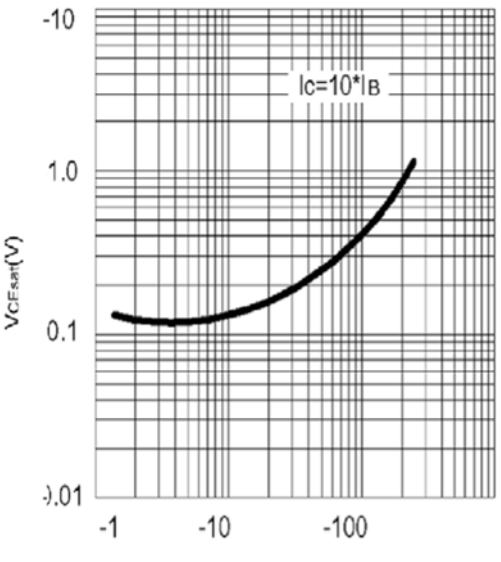
PARAMETER	TEST CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	I_C =100μA, I_E =0	$V_{(BR)CBO}$	-400	-	-	V
Collector-Emitter Breakdown Voltage	I_C = -1mA, I_B =0	$V_{(BR)CEO}$	-400	-	-	V
Emitter-Base Breakdown Voltage	I_E = -100μA, I_C =0	$V_{(BR)EBO}$	-5	-	-	V
Collector Cut-Off Current	V_{CB} = -400V, I_E =0	I_{CBO}	-	-	-0.1	μA
Emitter Cut-Off Current	V_{EB} = -4V, I_C =0	I_{EBO}	-	-	-0.1	μA
DC Current Gain[1]	V_{CE} = -10V, I_C = -1mA	h_{FE}	70	-	-	
	V_{CE} = -10V, I_C = -10mA		80	-	300	
	V_{CE} = -10V, I_C = -50mA		40	-	-	
	V_{CE} = -10V, I_C = -100mA		40	-	-	
Collector-Emitter Saturation Voltage[1]	I_C = -10mA, I_B = -1mA	$V_{CE(sat)}$	-	-	-0.2	V
	I_C = -50mA, I_B = -5mA		-	-	-0.3	V
Base-Emitter Saturation Voltage[1]	I_C = -10mA, I_B = -1mA	$V_{BE(sat)}$	-	-	-0.75	V
Transition frequency	V_{CE} = -20V, I_C = -10mA	f_T	50	-	-	MHz

Note:
1. Pulse test

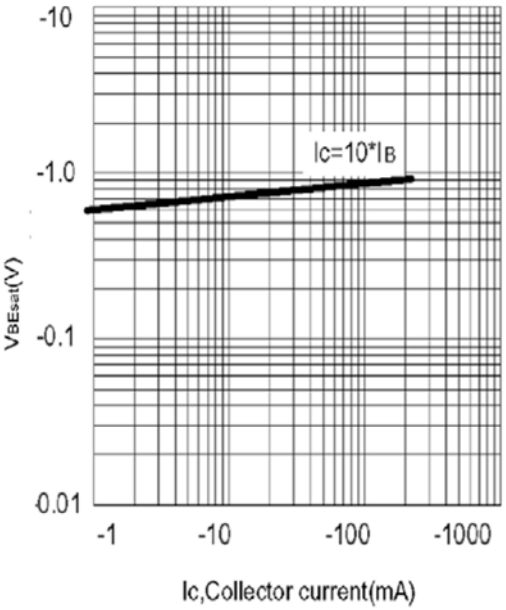
CHARACTERISTIC CURVES



DC CURRENT GAIN



COLLECTOR-EMITTER
SATURATION VOLTAGE



BASE-EMITTER